



4-18-05

IPW 2891  
JL

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. .... 10/072,415  
Filing Date ..... February 5, 2002  
Inventor ..... Ji Lee et al.  
Assignee ..... Micron Technology, Inc.  
Group Art Unit ..... 2891  
Examiner ..... V. Yevsikov  
Confirmation No. .... 5182  
Customer No. .... 021567  
Attorney's Docket No. .... MI30-068  
Title: Field Effect Transistor Fabrication Methods, Field Emission Device Fabrication Methods, and Field Emission Device Operational Methods

RESPONSE TO DECEMBER 15, 2004 OFFICE ACTION

To: Mail Stop Fee Amendment  
Assistant Commissioner for Patents  
P.O. Box 1450  
Alexandria VA 22313-1450

EV549572104

From: James D. Shaurette (Tel. 509-624-4276; Fax 509-838-3424)  
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Sir:

Responsive to the Office Action dated December 15, 2004, Applicants amend and  
remark as follows:

AMENDMENTS

04/19/2005 WABDELRI 00000004 10072415

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